



ACE7323M

P-Channel 20-V (D-S) MOSFET

Description

The ACE7323M uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. This device is suitable for use as a high side switch in SMPS and general purpose applications.

Features

- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (m Ω)	I_D (A)
-20	9 @ $V_{GS} = -4.5V$	-17
	12 @ $V_{GS} = -2.5V$	-14

Applications

- Load Switches
- DC/DC Conversion
- Motor Drives

Absolute Maximum Ratings

Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	± 8	V
Continuous Drain Current ^a	$T_A=25^\circ C$	I_D	-17	A
	$T_A=70^\circ C$		-12.2	
Pulse Drain Current ^b		I_{DM}	-60	
Continuous Drain Current (Diode Continuous) ^a		I_S	-5.1	A
Power Dissipation ^a	$T_A=25^\circ C$	P_D	3.5	W
	$T_A=70^\circ C$		2	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^\circ C$

Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$t \leq 10sec$	$R_{\theta JA}$	35	$^\circ C/W$
	Steady State		81	$^\circ C/W$

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature



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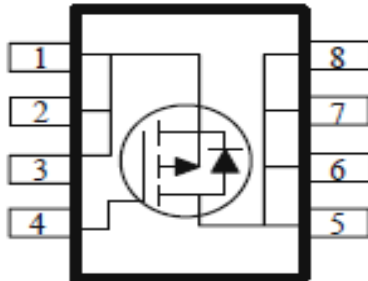
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Packaging Type

DFN3*3-8L

Ordering information

ACE7323M XX + H



Halogen - free
 Pb - free
 NN : DFN3*3-8L

Electrical Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Source Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4			V
Gate Body Leakage	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 8V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-16V, V_{GS}=0V$			-1	uA
		$V_{DS}=-16V, V_{GS}=0V, T_J=55^\circ C$			-25	
On-State Drain-Current ^a	$I_{D(on)}$	$V_{DS}=-5V, V_{GS}=-4.5V$	-25			A
Static Drain-Source On-Resistance ^a	$r_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-12.9A$			9-12	mΩ
		$V_{GS}=-2.5V, I_D=-10.4A$				
Forward Transconductance ^a	g_{fS}	$V_{DS}=-15V, I_D=-12.9A$		9		S
Diode Forward Voltage ^a	V_{SD}	$I_S=-2.6A, V_{GS}=0V$		-0.66		V
Dynamic ^b						
Total Gate Charge	Q_g	$V_{DS}=-10V, V_{GS}=-4.5V, I_D=-12.9A$		82		nC
Gate-Source Charge	Q_{gs}			14		
Gate-Drain Charge	Q_{gd}			19		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=-10V, R_L=0.8\Omega, I_D=-12.9A, V_{GEN}=-4.5V, R_{GEN}=6\Omega,$		24		ns
Rise Time	t_f			46		
Turn-Off Delay Time	$t_{d(off)}$			326		
Fall Time	t_f			133		
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$		6507		pF
Output Capacitance	C_{oss}			570		
Reverse Transfer Capacitance	C_{rss}			512		

Note:

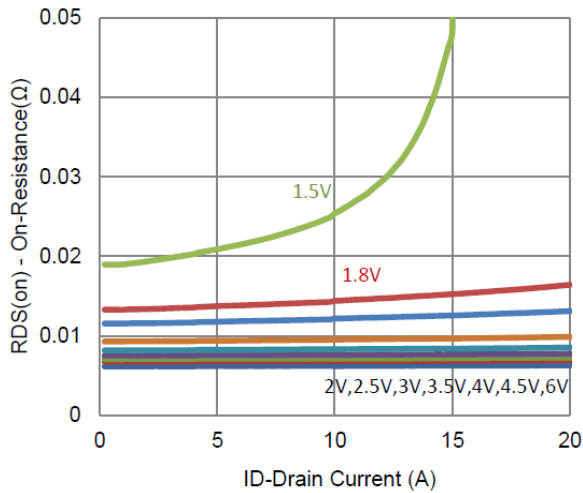
- a. Pulse test: PW ≤ 300us duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.



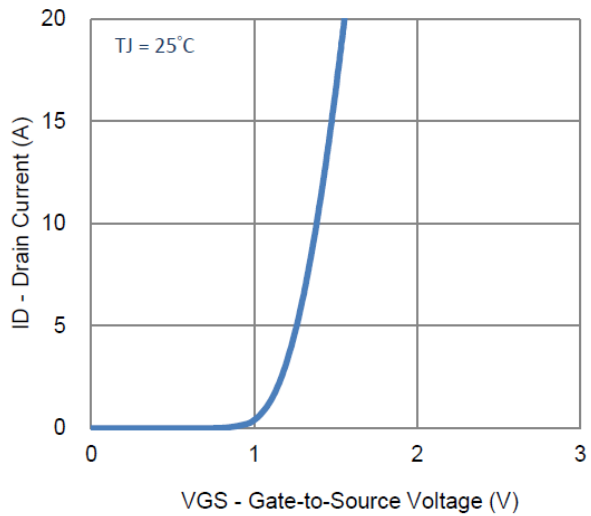
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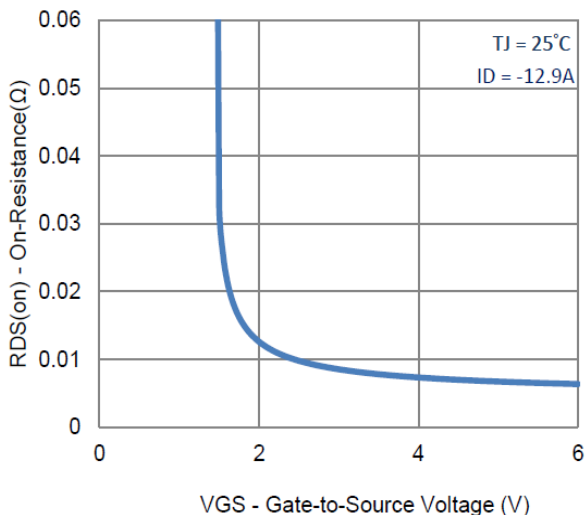
Typical Electrical Characteristics



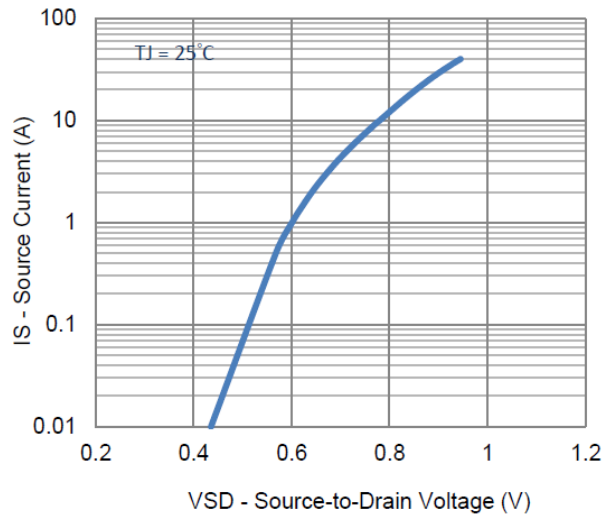
1. On-Resistance vs. Drain Current



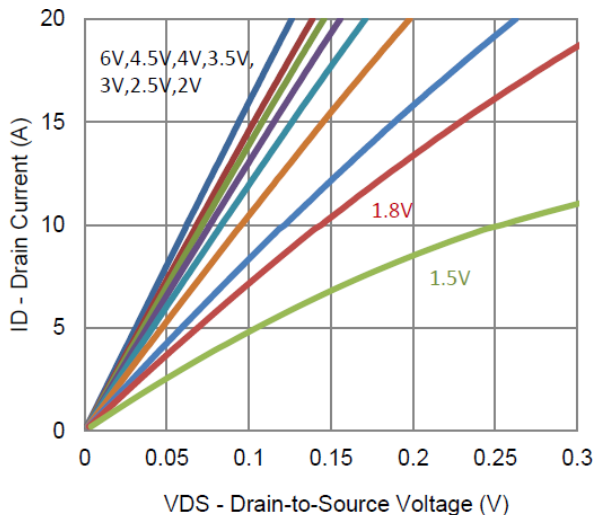
2. Transfer Characteristics



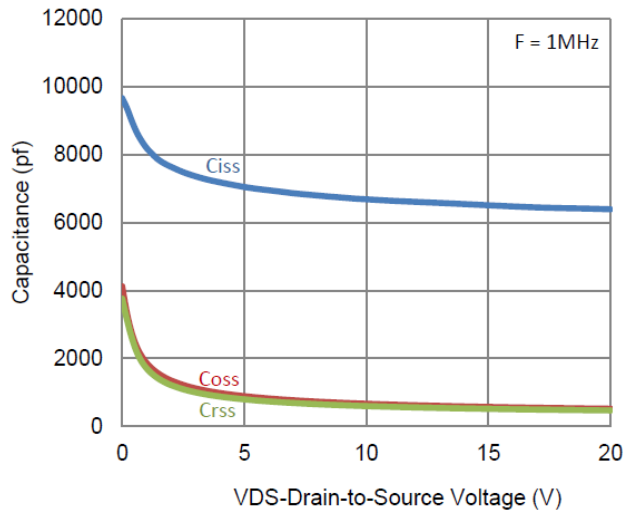
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage



5. Output Characteristics

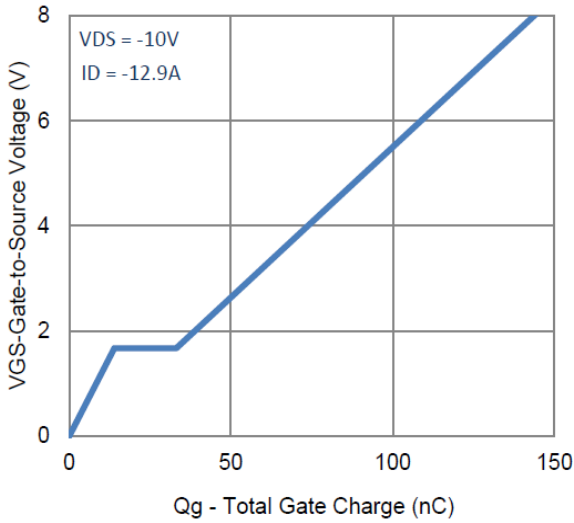


6. Capacitance

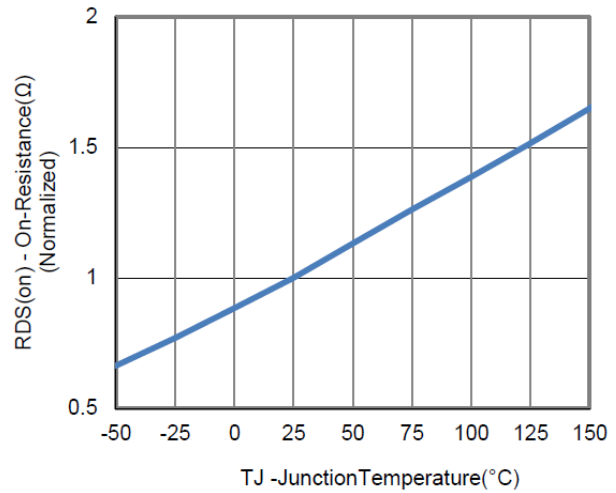


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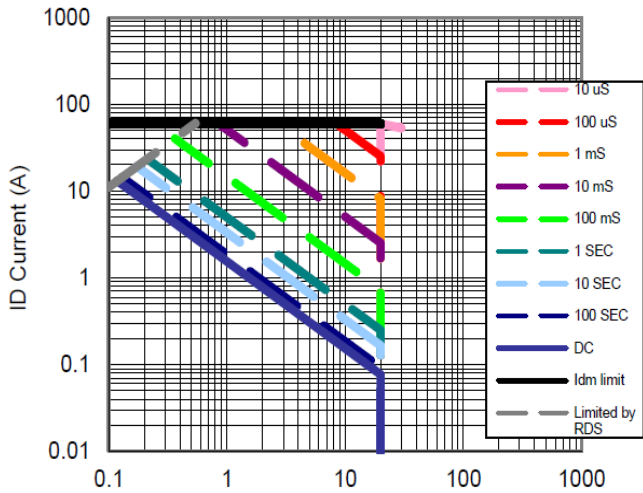
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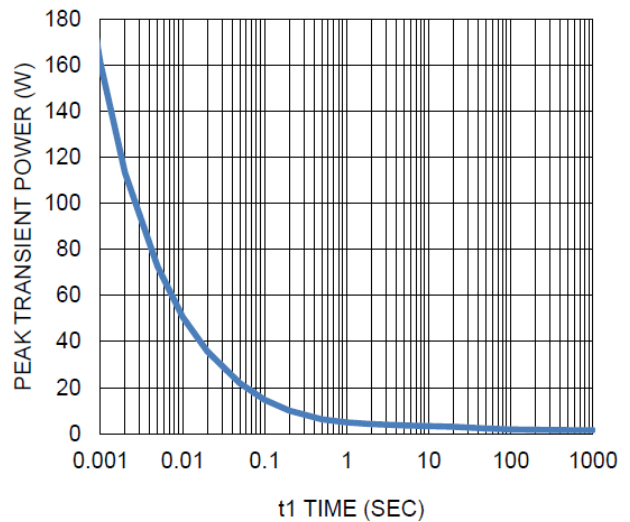
7. Gate Charge



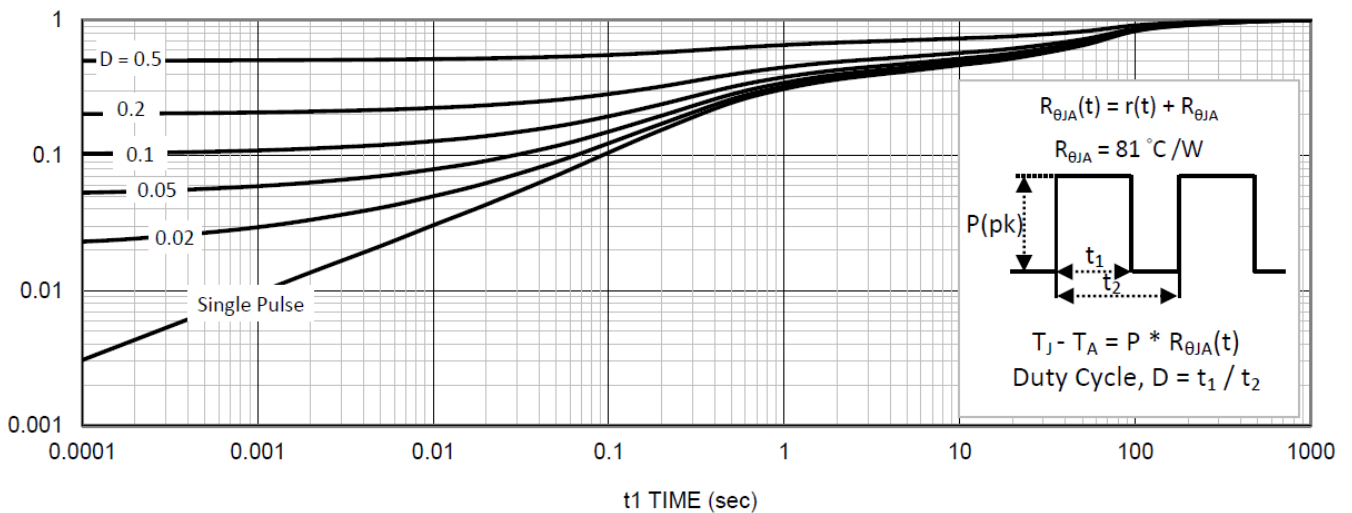
8. Normalized On-Resistance vs Junction Temperature



9. Safe Operating Area



10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

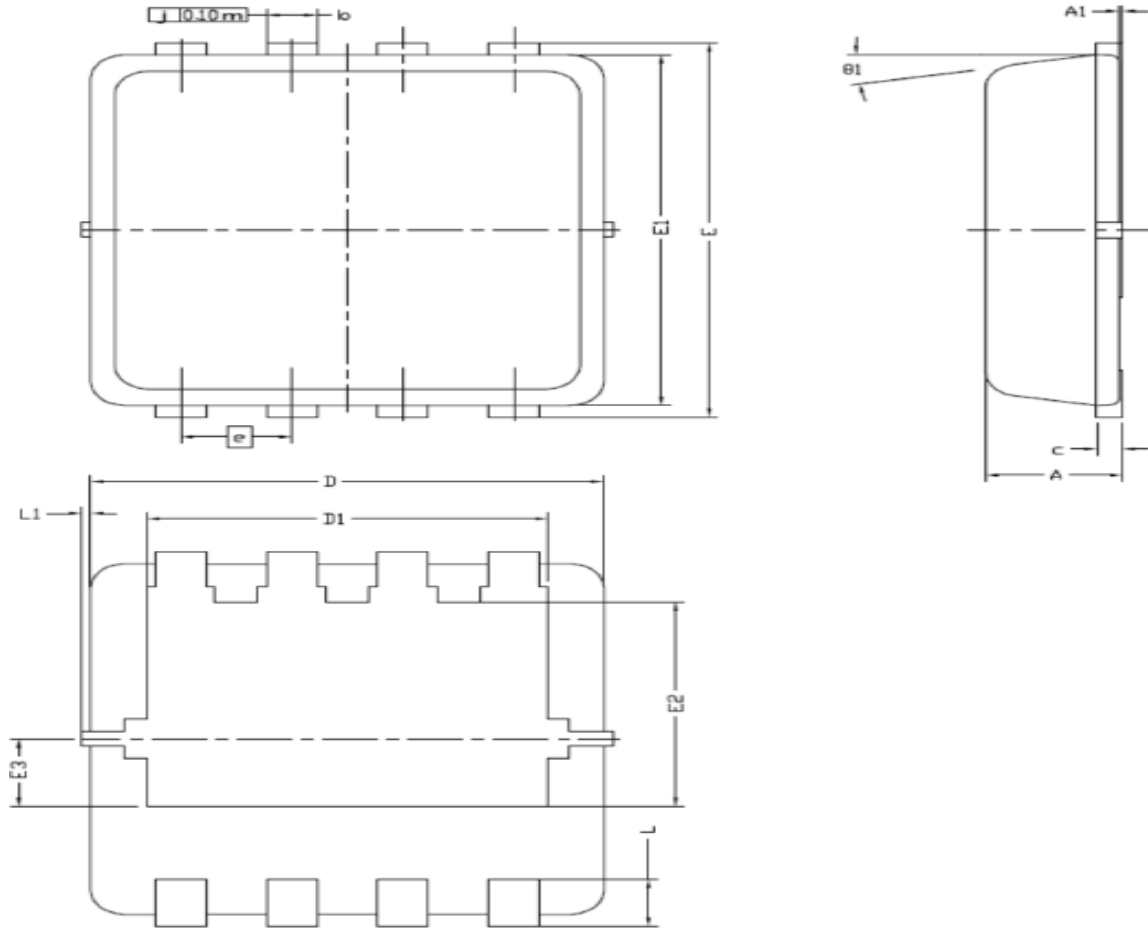


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Packing Information

DFN3*3-8L



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.80	0.900	0.0276	0.0315	0.0354
A1	0.00		0.05	0.000		0.002
b	0.24	0.30	0.35	0.009	0.012	0.014
c	0.10	0.152	0.25	0.004	0.006	0.010
D	3.00 BSC			0.118 BSC		
D1	2.35 BSC			0.093 BSC		
E	3.20 BSC			0.126 BSC		
E1	3.00 BSC			0.118 BSC		
E2	1.75 BSC			0.069 BSC		
E3	0.575 BSC			0.023 BSC		
e	0.65 BSC			0.026 BSC		
L	0.30	0.40	0.50	0.0018	0.0157	0.0197
L1	0		0.100	0		0.004
θ1	0°	10°	12°	0°	10°	12°



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Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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